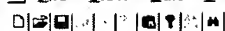


I. Number	Hits	Search Text	DB	Time stamp
1	45245	bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:33
2	707	buried adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:34
3	1	multilayer\$3 adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:48
4	0	different adj doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:49
5	0	multiple adj doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 10:50
6	94	(buried adj bit adj line) and multiple	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 16:53
7	0	multiple adj doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 11:23
8	8	doping adj bit adj line	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 13:07
9	6	"6054226"	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 13:07
10	1	"6054226" and (Tantalum or Ta) and (hafnium or hf)	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 14:56
11	27	"5966012"	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 14:57
13	29	((buried adj bit adj line) and doping and deep) and shallow	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 16:54

12	65	(buried adj bit adj line) and doping and deep	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:27
15	0	(composite adj doping) and (bit adj line)	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:28
14	25	composite adj doping	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:30
16	68	deep adj doping	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:30
17	129	shallow adj doping	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:31
18	13	(deep adj doping) and (shallow adj doping)	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:31
19	3	(bit adj line) and ((deep adj doping) and (shallow adj doping))	USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM_TDB	2003/06/11 17:31



- ☒ BRS:
- ☒ BRS:
- ☒ BRS: upside
- ☐ Pending
- ☒ Active
 - ☒ L1: (45245) bit adj line
 - ☒ L2: (707) buried adj bit adj line
 - ☒ L3: (1) multilayer\$3 adj bit adj line
 - ☒ L4: (0) different adj doping adj bit adj line
 - ☒ L5: (0) multiple adj doping adj bit adj line
 - ☒ L6: (94) 2 and multiple
 - ☒ L7: (0) multiple adj doping adj bit adj line
 - ☒ L8: (8) doping adj bit adj line
 - ☒ L9: (6) "6054226"
 - ☒ L10: (1) 9 and (Tantalum or Ta) and (hafnium or hf,
 - ☒ L11: (27) "5966012"
 - ☒ L13: (29) 12 and shallow
 - ☒ L12: (65) 2 and doping and deep
 - ☒ L15: (0) 14 and 1
 - ☒ L14: (25) composite adj doping
 - ☒ L16: (68) deep adj doping
 - ☒ L17: (129) shallow adj doping
 - ☒ L18: (13) 16 and 17
 - ☒ L19: (3) 1 and 18
- ☐ Failed

DB: USPAT; US-PGPUB; EPD; JPO; DERWENT; IBM; TDB

Default operator: OR

☐ Plurals☒ Highlight all hit terms initially

1 and 18

☒ BRS form ☐ B&B form ☐ Image ☐ Text ☐ HTML

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Cla	Inventor	S	C	P	3	Image Do
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20020181287 A1	20021205	10	Channel write/erase flash memory cell 365/185.29 and its manufacturing method	365/185.18			Hsu, Chung-Hsiang et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200201
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020136058 A1	20020926	10	Channel write/erase flash memory cell 365/185.18 and its manufacturing method				Hsu, Ching-Hsiang et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200201
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6501685 B2	20021231	10	Channel write/erase flash memory cell 365/185.33 and its manufacturing method	257/315; 257/316;			Hsu, Ching-Hsiang et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 650168

☒ HTML ☐ Details ☐ HTML

Ready

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